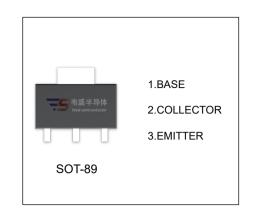


A44 TRANSISTOR (NPN)

FEATURES

- Low Collector-Emitter Saturation Voltage
- High Breakdown Voltage



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{\sf CBO}$	Collector-Base Voltage	400	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	6	V
Ic	Collector Current -Continuous	200	mA
Ісм	Collector Current -Pulsed	300	mA
Pc	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	250	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA,I _E =0	400			V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	I _C =1mA,I _B =0	400			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA,I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =400V,I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V,I _C =0			0.1	μA
	h _{FE(1)} *	V _{CE} =10V, I _C =1mA	40			
DC ourrent gain	h _{FE(2)} *	V _{CE} =10V, I _C =10mA	50		200	
DC current gain	h _{FE(3)} *	V _{CE} =10V, I _C =50mA	45			
	h _{FE(4)} *	V _{CE} =10V, I _C =100mA	40			
	V _{CE(sat)} *	I _C =1mA,I _B =0.1mA			0.4	V
Collector-emitter saturation voltage		I _C =10mA,I _B =1mA			0.5	V
		I _C =50mA,I _B =5mA			0.75	V
Base-emitter saturation voltage	V _{BE(sat)} *	I _C =10mA,I _B =1mA			0.75	V
Collector output capacitance	C _{ob}	V _{CB} =20V, I _E =0, f=1MHz			7	pF
Emitter input capacitance	C _{ib}	V _{BE} =0.5V, I _C =0, f=1MHz			130	pF

^{*}Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.



